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Attorney Docket SEL 192

PENTHE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of Yamazaki et al.	I hereby certify that this correspondence is being
Serial No.: 09/610,217)	deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents,
Filed: July 5, 2000)	P.O. Box 1450, Alexandria, VA 22313-1450 on
For: Semiconductor Device And) Fabrication Method Thereof)	(Date of Deposit) Shannon Wallace Name of applicant, assignee, or Registered Rep.
Art Unit: 2812	Sanno Wollaw 7/2/03
Examiner: R. Booth)	Signature Date

MAIL STOP AF Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

July 2, 2003

AMENDMENT B (AFTER FINAL)

Sir:

In response to the Final Rejection of March 6, 2003, a one month extension of time being separately submitted, please enter the following amendment in the above-identified application.

IN THE CLAIMS:

Please amend the claims as follows:

29 (Twice Amended). A method of fabricating a semiconductor device comprising:

forming a first semiconductor island and a second semiconductor island and a third semiconductor island over a substrate;

forming a first low concentration n-type impurity region and a second low concentration n-type impurity region and a third low concentration n-type impurity region respectively in said first semiconductor island and said second semiconductor island and said third semiconductor island by